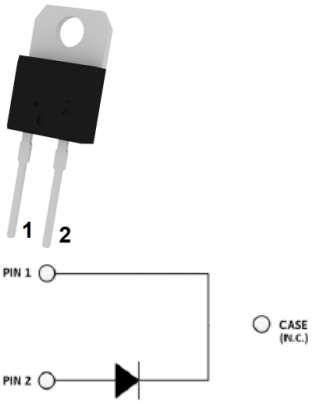
PRELIMINARY DATASHEET 规格书

SCD012TM065S22F

3th Generation 650V/12A SiC Schottky Barrier Diode
第三代 650V/12A 碳化硅肖特基二极管
Package Type: TO-220N-2L



Pin 1 Cathode
Pin 2 Anode

V_{RRM} = 650 V
I_F (135 °C) = 15 A
V_F (25 °C) = 1.35 V

- High-speed switching performance
  高速开关表现
- No reverse recovery
  无反向恢复

Maximum ratings 最大额定值[1] [2]

PARAMETER 参数	SYMBOL 符号	CONDITIONS 条件	MIN 最小	MAX 最大	UNIT 单位
Repetitive peak reverse voltage 重复反向峰值电压	V_{RRM}	T_{vj} ≥ 25 °C		650	V
Surge peak reverse voltage 浪涌峰值反向电压	V_{RSM}			650	V
DC reverse voltage 直流反向电压	V_{DC}			650	V
Continuous forward current 连续正向电流	I_F	T_C = 25 °C		33	A
		T_C = 135 °C		15	A
		T_C = 144 °C		12	A
Surge non-repetitive forward current 非重复正向浪涌电流	I_{FSM}	T_C = 25 °C, t_p = 10 ms, half sine pulse		111	A
Repetitive peak forward current 重复峰值正向电流	I_{FRM}	T_C = 25 °C, t_p = 10 ms, half sine wave D = 0.1		74	A
Power dissipation 耗散功率	P_{tot}			90	W
i^2t value 安秒平方值	$\int i^2dt$	T_C = 25 °C, t_p = 10 ms		62	A^2s
Operation junction temperature 工作结温范围	T_{vj}		-55	175	°C
Storage temperature 存储温度范围	T_{stg}		-55	175	°C

Scan for latest product catalogue 扫描查看最新产品目录

[1] Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747
[1] 根据标准 IEC 60747 要求，最大额定值表示超过该限值可能会对器件造成损坏
[2] T_{vj} = 25 °C, unless otherwise specified / 除非另有规定, T_{vj} = 25 °C

SiC Diode[3] [4]

PARAMETER 参数	SYMBOL 符号	CONDITIONS 条件		MIN 最小	TYP 典型	MAX 最大	UNIT 单位
DC blocking voltage 直流击穿电压	V_{DC}	I_R = 1 mA		650			V
Forward voltage 正向导通压降	V_F	I_F = 12 A	T_{vj} = 25 °C		1.35	1.50	V
			T_{vj} = 175 °C		1.60	1.80	V
Reverse current 反向电流	I_R	V_R = 650 V	T_{vj} = 25 °C		1	36	µA
			T_{vj} = 175 °C		10	96	µA
Total capacitance 总电容	C	f =1 MHz	VR = 0 V		650		pF
			VR = 200 V		72		pF
			VR = 400 V		66		pF
Total capacitive charge 总电容电荷	Q_C	V_R =400 V (∫C(V)dV)			36		nC
Capacitance stored energy 电容储存能量	E_C	V_R =400 V (∫Q_C(V)dV)			5.7		µJ

Package properties 封装特性

PARAMETER 参数	SYMBOL 符号	CONDITIONS 条件	MIN 最小	TYP 典型	MAX 最大	UNIT 单位
Thermal resistance from junction to case 结到壳热阻	$R_{th(j-c)}$			1.68		K/W

[3] Characteristic values according to IEC 60747-2 / 特性值依据 IEC 60747-2
[4] T_{vj} = 25 °C, unless otherwise specified / 除非另有规定, T_{vj} = 25 °C

Characteristics 特性曲线

Figure 1. Forward characteristics
图 1. 正向特性
$I_F = f(V_F)$

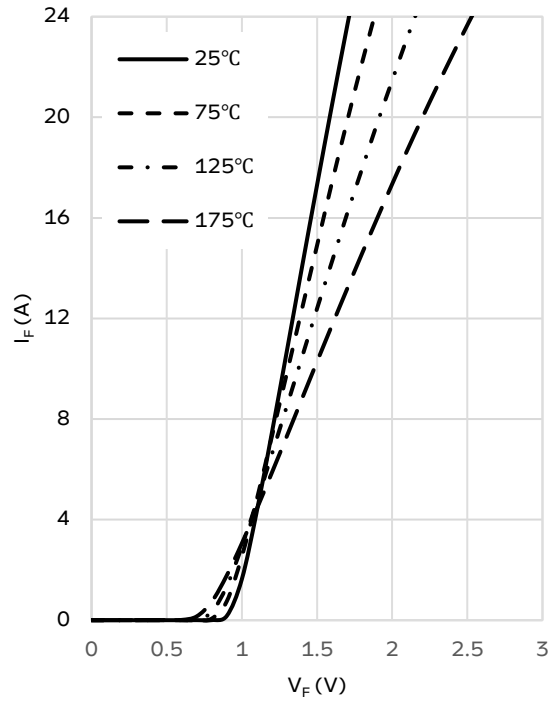


Figure 2. Reverse characteristics
图 2. 反向特性
$I_R = f(V_R)$

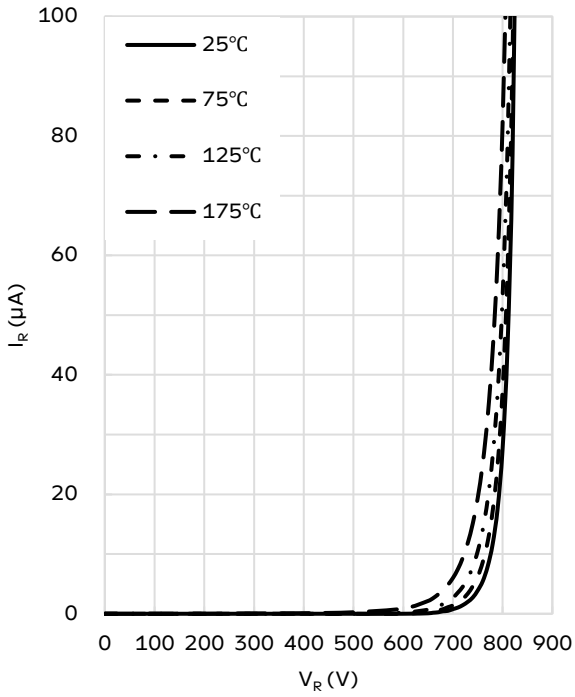


Figure 3. Current derating
图 3. 电流降额
$I_{F(peak)} = f(Tc)$

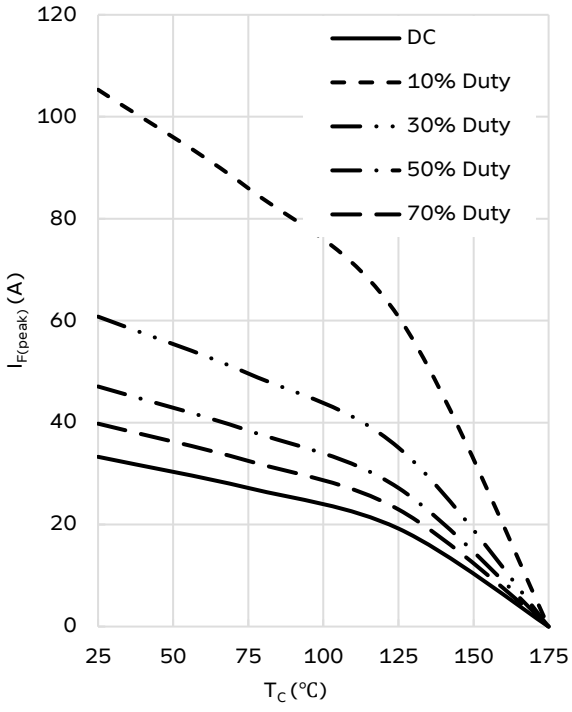


Figure 4. Power derating
图 4. 功率降额
$P_{tot} = f(T_C)$

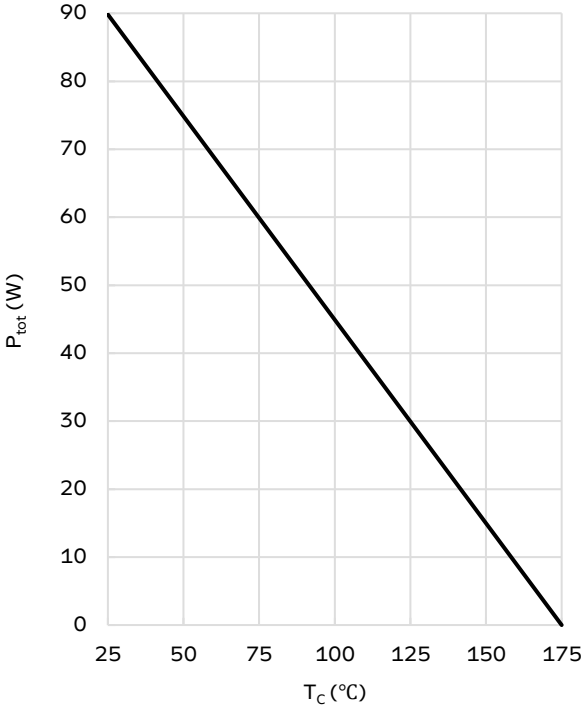


Figure 5. Capacitance vs. reverse voltage
图 5. 电容 vs 反向电压
$C = f(V_R)$

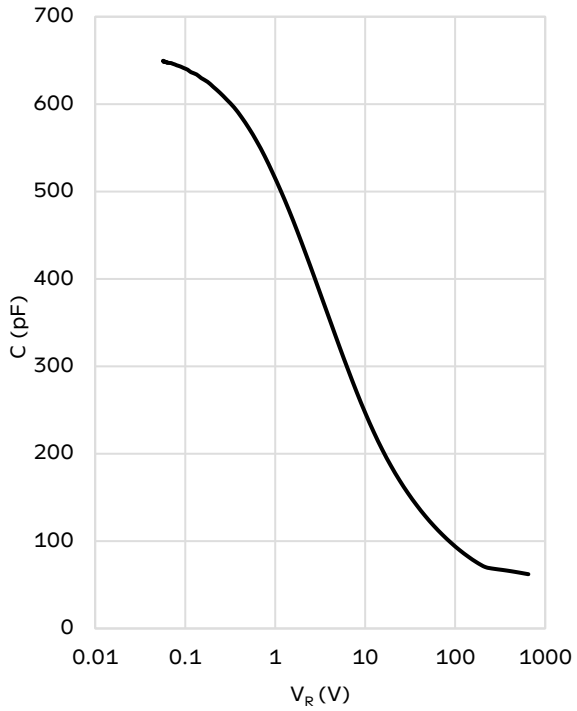


Figure 6. Total capacitance charge vs. reverse voltage
图 6. 总电容电荷 vs 反向电压
$Q_C = f(V_R)$

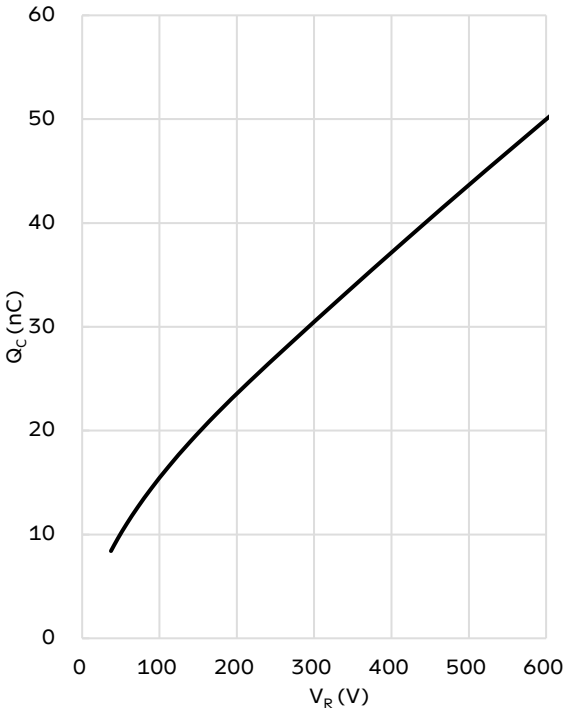
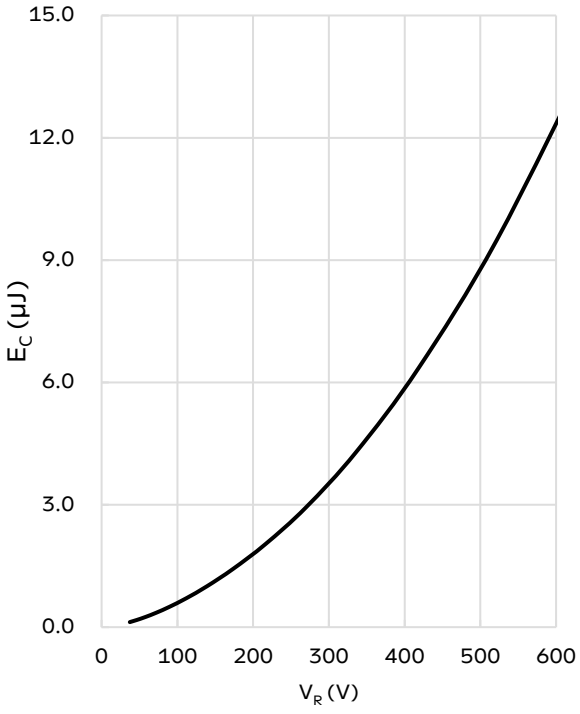
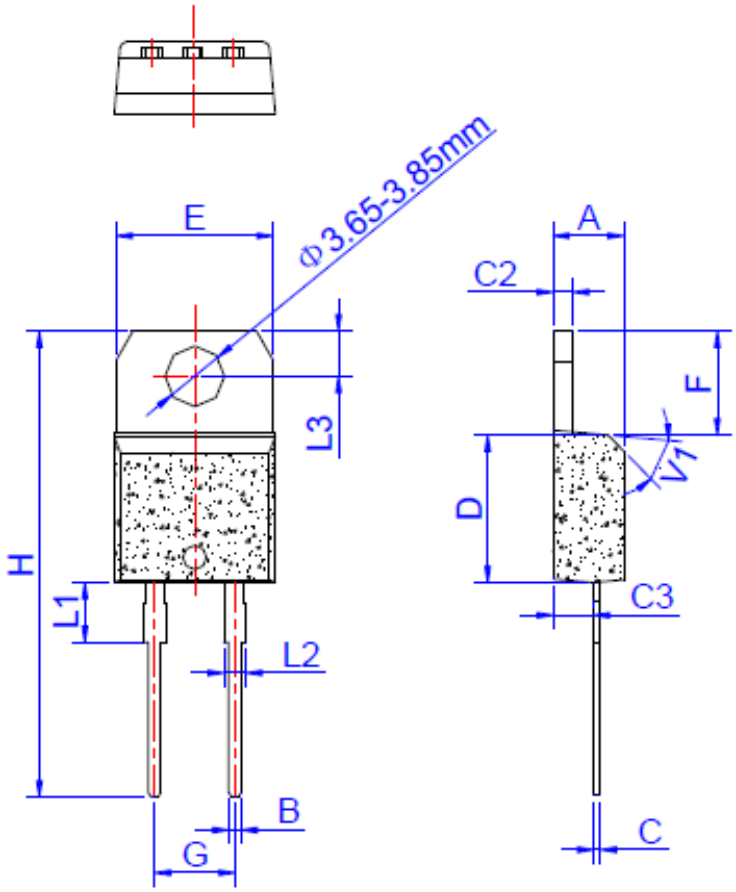


Figure 7. Capacitance stored energy
图 7. 电容储存能量
$E_C = f(V_R)$



Outline drawing 外形图

Marking SCDS22F012TM065



Sym-bol	Dimensions In Milli-meters	
	Min.	Max.
A	4.40	4.60
B	0.61	0.88
C	0.46	0.70
C2	1.21	1.32
C3	2.40	2.72
D	8.60	9.70
E	9.80	10.4
F	6.55	6.95
G	TYP 5.08	
H	28.0	29.8
L1	TYP 3.75	
L2	1.14	1.70
L3	2.65	2.95
V1	TYP 45°	

This is an electrostatic sensitive device. 本产品对静电特别敏感.
This product has been designed and qualified for industry Level. 本产品的设计符合工业级标准.
Note: All dimensions are in mm

Ordering Information 订购信息

OPTION 选项		ARTICLE NUMBER 商品编号
Qualification grade	Industrial (F)	SCD012TM065S22**F**
Packaging Method 包装方式	Tube (_P20)	SCD012TM065S22**F _P20**

Revision History 修订历史

Release 发布	Version 版本	Description 描述
2026-07-23	v1.0	Preliminary Datasheet 初始规格书